Quad Analog Switch/ Multiplexer/Demultiplexer with Separate Analog and Digital Power Supplies

High-Performance Silicon-Gate CMOS

The MC74HC4316A utilizes silicon–gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF–channel leakage current. This bilateral switch/multiplexer/demultiplexer controls analog and digital voltages that may vary across the full analog power–supply range (from V_{CC} to V_{EE}).

The HC4316A is similar in function to the metal–gate CMOS MC14016 and MC14066, and to the High–Speed CMOS HC4066A. Each device has four independent switches. The device control and Enable inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs. The device has been designed so that the ON resistances ($R_{\rm ON}$) are much more linear over input voltage than $R_{\rm ON}$ of metal–gate CMOS analog switches. Logic–level translators are provided so that the On/Off Control and Enable logic–level voltages need only be $V_{\rm CC}$ and GND, while the switch is passing signals ranging between $V_{\rm CC}$ and $V_{\rm EE}$. When the Enable pin (active–low) is high, all four analog switches are turned off.

Features

- Logic-Level Translator for On/Off Control and Enable Inputs
- Fast Switching and Propagation Speeds
- High ON/OFF Output Voltage Ratio
- Diode Protection on All Inputs/Outputs
- Analog Power–Supply Voltage Range $(V_{CC} V_{EE}) = 2.0$ to 12.0 V
- Digital (Control) Power–Supply Voltage Range
 (V_{CC} GND) = 2.0 V to 6.0 V, Independent of V_{EE}
- Improved Linearity of ON Resistance
- Chip Complexity: 66 FETs or 16.5 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable*
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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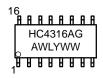


SOIC-16 D SUFFIX CASE 751B

PIN ASSIGNMENT

X _A [1●	16] V _{CC}
Y _A [2	15	A ON/OFF CONTROL
Y _B [3	14	D ON/OFF CONTROL
X _B [4	13	XD
B ON/OFF CONTROL	5	12] Y _D
C ON/OFF CONTROL	6	11] Y _C
ENABLE [7	10] x _c
GND [8	9] V _{EE}
			•

MARKING DIAGRAM



A = Assembly Location

 $\begin{array}{lll} \text{WL, L} &=& \text{Wafer Lot} \\ \text{YY, Y} &=& \text{Year} \\ \text{WW, W} &=& \text{Work Week} \\ \text{G} &=& \text{Pb-Free Package} \end{array}$

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC4316ADR2G	SOIC-16 (Pb-Free)	2500/ Tape&Reel
NLV74HC4316ADR2G*	SOIC-16 (Pb-Free)	2500/ Tape&Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

FUNCTION TABLE

Inp	State of Analog	
Enable	On/Off Control	Switch
L L H	H L X	On Off Off

X = Don't Care.

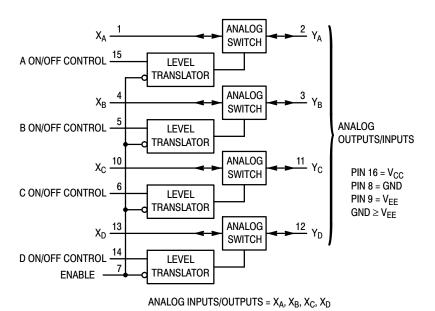


Figure 1. Logic Diagram

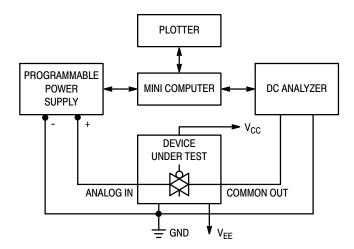


Figure 2. On Resistance Test Set-Up

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage (Ref. to GND) (Ref. to V_{EE})	-0.5 to +7.0 -0.5 to +14.0	V
V _{EE}	Negative DC Supply Voltage (Ref. to GND)	-7.0 to +0.5	V
V _{IS}	Analog Input Voltage	V _{EE} – 0.5 to V _{CC} + 0.5	V
V _{in}	DC Input Voltage (Ref. to GND)	-0.5 to $V_{CC} + 0.5$	V
I	DC Current Into or Out of Any Pin	±25	mA
P _D	Power Dissipation in Still Air SOIC Package*	500	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds)	260	°C

 V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open. I/O pins must be connected to a

properly terminated line or bus.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

*Derating - SOIC Package: -7 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage (Ref. to GND)	2.0	6.0	V
V _{EE}	Negative DC Supply Voltage (Ref. to GND)	-6.0	GND	V
V _{IS}	Analog Input Voltage	V _{EE}	V _{CC}	V
V _{in}	Digital Input Voltage (Ref. to GND)	GND	V _{CC}	V
V _{IO} *	Static or Dynamic Voltage Across Switch	-	1.2	V
T _A	Operating Temperature, All Package Types	-55	+125	°C
t _r , t _f		V 0 V 0	1000 600 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS Digital Section (Voltages Referenced to GND) VEE = GND Except Where Noted

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC}	–55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Voltage, Control or Enable Inputs	R _{on} = Per Spec	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low–Level Voltage, Control or Enable Inputs	R _{on} = Per Spec	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
I _{in}	Maximum Input Leakage Current, Control or Enable Inputs	$V_{in} = V_{CC}$ or GND $V_{EE} = -6.0 \text{ V}$	6.0	±0.1	±1.0	±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$\label{eq:Vin} \begin{aligned} V_{\text{in}} &= V_{\text{CC}} \text{ or GND} \\ V_{\text{IO}} &= 0 \text{ V} & V_{\text{EE}} &= \text{GND} \\ & V_{\text{EE}} &= -6.0 \end{aligned}$	6.0 6.0	2 4	20 40	40 160	μΑ

^{*}For voltage drops across the switch greater than 1.2 V (switch on), excessive V_{CC} current may be drawn; i.e., the current out of the switch may contain both V_{CC} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

DC ELECTRICAL CHARACTERISTICS Analog Section (Voltages Referenced to V_{EE})

					Gua	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC}	V _{EE}	–55 to 25°C	≤ 85 °C	≤ 125°C	Unit
R _{on}	Maximum "ON" Resistance	$\begin{aligned} &V_{in} = V_{IH} \\ &V_{IS} = V_{CC} \text{ to } V_{EE} \\ &I_{S} \leq 2.0 \text{ mA (Figure 2)} \end{aligned}$	2.0* 4 5 4.5 6.0	0.0 0.0 -4.5 -6.0	- 160 90 90	- 200 110 110	- 240 130 130	Ω
		$V_{\text{in}} = V_{\text{IH}}$ $V_{\text{IS}} = V_{\text{CC}}$ or V_{EE} (Endpoints) $I_{\text{S}} \le 2.0$ mA (Figure 2)	2.0 4.5 4.5 6.0	0.0 0.0 -4.5 -6.0	- 90 70 70	- 115 90 90	- 140 105 105	
ΔR_{on}	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$\begin{aligned} &V_{in} = V_{IH} \\ &V_{IS} = 1/2 \; (V_{CC} - V_{EE}) \\ &I_{S} \leq 2.0 \; \text{mA} \end{aligned}$	2.0 4.5 4.5 6.0	0.0 0.0 -4.5 -6.0	- 20 15 15	- 25 20 20	- 30 25 25	Ω
l _{off}	Maximum Off-Channel Leakage Current, Any One Channel	$V_{in} = V_{IL}$ $V_{IO} = V_{CC}$ or V_{EE} Switch Off (Figure 3)	6.0	-6.0	0.1	0.5	1.0	μΑ
I _{on}	Maximum On-Channel Leakage Current, Any One Channel	$V_{in} = V_{IH}$ $V_{IS} = V_{CC}$ or V_{EE} (Figure 4)	6.0	-6.0	0.1	0.5	1.0	μΑ

^{*}At supply voltage (V_{CC} – V_{EE}) approaching 2.0 V the analog switch–on resistance becomes extremely non–linear. Therefore, for low–voltage operation, it is recommended that these devices only be used to control digital signals.

$\textbf{AC ELECTRICAL CHARACTERISTICS} \ (C_L = 50 \ \text{pF, Control or Enable} \ t_r = t_f = 6 \ \text{ns, V}_{EE} = \text{GND})$

			Gu			
Symbol	Parameter	v _{cc}	–55 to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Analog Input to Analog Output (Figures 8 and 9)	2.0 4.5 6.0	40 6 5	50 8 7	60 9 8	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Control or Enable to Analog Output (Figures 10 and 11)	2.0 4.5 6.0	130 40 30	160 50 40	200 60 50	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Control or Enable to Analog Output (Figures 10 and 11)	2.0 4.5 6.0	140 40 30	175 50 40	250 60 50	ns
С	Maximum Capacitance ON/OFF Control and Enable Inputs	-	10	10	10	pF
	Control Input = GND Analog I/O Feedthrough		35 1.0	35 1.0	35 1.0	

		Typical @ 25°C, V _{CC} = 5.0 V	
Cpn	Power Dissipation Capacitance (Per Switch) (Figure 13)*	15	рF

^{*}Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)

Symbol	Parameter	Test Conditions	V _{CC} V	V _{EE} V	Limit* 25°C	Unit
BW	BW Maximum On–Channel Bandwidth or Adjust $f_{in} = 1$ MHz Sine Wave Adjust f_{in} Voltage to Obtain 0 dBm at V_{OS} Increase f_{in} Frequency Until dB Meter Reads -3 dB $R_L = 50 \Omega$, $C_L = 10 pF$				150 160 160	MHz
_	Off-Channel Feedthrough Isolation (Figure 6)	$ \begin{aligned} f_{in} &\equiv \text{Sine Wave} \\ \text{Adjust } f_{in} &\text{ Voltage to Obtain 0 dBm at V}_{IS} \\ f_{in} &= \text{10 kHz}, \ R_L = 600 \ \Omega, \ C_L = 50 \ pF \end{aligned} $	2.25 4.50 6.00	-2.25 -4.50 -6.00	-50 -50 -50	dB
		f_{in} = 1.0 MHz, R_L = 50 Ω , C_L = 10 pF	2.25 4.50 6.00	-2.25 -4.50 -6.00	-40 -40 -40	
-	Feedthrough Noise, Control to Switch (Figure 7)	$\begin{split} V_{in} & \leq 1 \text{ MHz Square Wave } (t_r = t_f = 6 \text{ ns}) \\ \text{Adjust R}_L \text{ at Setup so that } I_S = 0 \text{ A} \\ R_L & = 600 \ \Omega, \ C_L = 50 \text{ pF} \end{split}$	2.25 4.50 6.00	-2.25 -4.50 -6.00	30 65 100	mV_PP
		$R_L = 10 \text{ k}\Omega$, $C_L = 10 \text{ pF}$	2.25 4.50 6.00	-2.25 -4.50 -6.00	60 130 200	
-	Crosstalk Between Any Two Switches (Figure 12)	$ \begin{aligned} f_{in} &\equiv \text{Sine Wave} \\ \text{Adjust } f_{in} &\text{ Voltage to Obtain 0 dBm at V}_{IS} \\ f_{in} &= 10 \text{ kHz}, \text{ R}_{L} = 600 \ \Omega, \text{ C}_{L} = 50 \text{ pF} \end{aligned} $	2.25 4.50 6.00	-2.25 -4.50 -6.00	-70 -70 -70	dB
		f_{in} = 1.0 MHz, R_L = 50 Ω , C_L = 10 pF	2.25 4.50 6.00	-2.25 -4.50 -6.00	-80 -80 -80	
THD	Total Harmonic Distortion (Figure 14)	$\begin{split} f_{in} = 1 \text{ kHz, } R_L = 10 \text{ k}\Omega, C_L = 50 \text{ pF} \\ \text{THD} = \text{THD}_{Measured} - \text{THD}_{Source} \\ V_{IS} = 4.0 \text{ V}_{PP} \text{ sine wave} \\ V_{IS} = 8.0 \text{ V}_{PP} \text{ sine wave} \\ V_{IS} = 11.0 \text{ V}_{PP} \text{ sine wave} \end{split}$	2.25 4.50 6.00	-2.25 -4.50 -6.00	0.10 0.06 0.04	%

^{*}Limits not tested. Determined by design and verified by qualification.

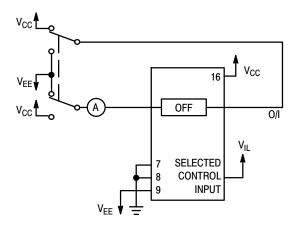


Figure 3. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

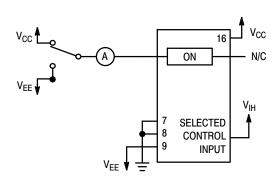
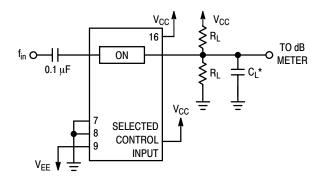
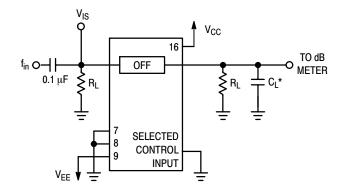


Figure 4. Maximum On Channel Leakage Current, Test Set-Up



^{*}Includes all probe and jig capacitance.

Figure 5. Maximum On-Channel Bandwidth Test Set-Up



*Includes all probe and jig capacitance.

Figure 6. Off-Channel Feedthrough Isolation, Test Set-Up

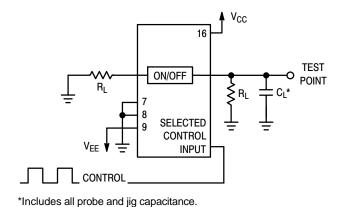


Figure 7. Feedthrough Noise, Control to Analog Out, Test Set-Up

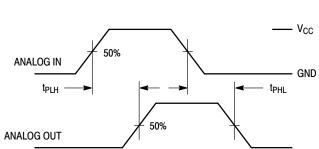
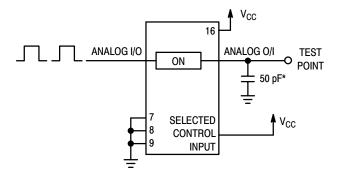
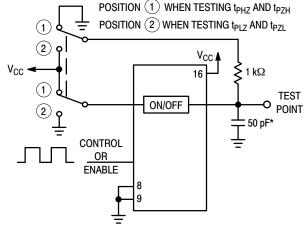


Figure 8. Propagation Delays, Analog In to Analog Out



*Includes all probe and jig capacitance.

Figure 9. Propagation Delay Test Set-Up



*Includes all probe and jig capacitance.

Figure 11. Propagation Delay Test Set-Up

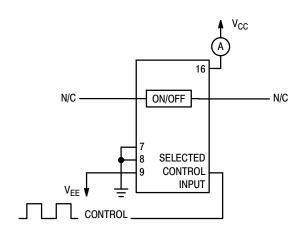


Figure 13. Power Dissipation Capacitance
Test Set-Up

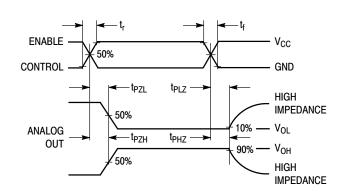
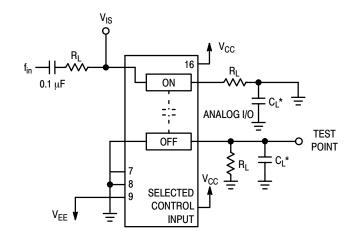
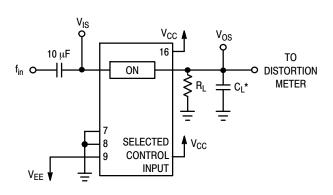


Figure 10. Propagation Delay, ON/OFF Control to Analog Out



*Includes all probe and jig capacitance.

Figure 12. Crosstalk Between Any Two Switches, Test Set-Up (Adjacent Channels Used)



*Includes all probe and jig capacitance.

Figure 14. Total Harmonic Distortion, Test Set-Up

APPLICATIONS INFORMATION

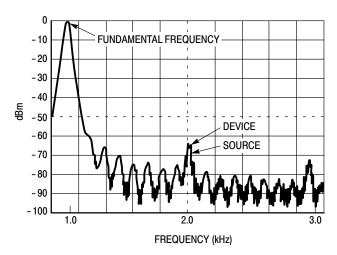


Figure 15. Plot, Harmonic Distortion

The Enable and Control pins should be at V_{CC} or GND logic levels, V_{CC} being recognized as logic high and GND being recognized as a logic low. Unused analog inputs/outputs may be left floating (not connected). However, it is advisable to tie unused analog inputs and outputs to V_{CC} or V_{EE} through a low value resistor. This minimizes crosstalk and feedthrough noise that may be picked up by the unused I/O pins.

The maximum analog voltage swings are determined by the supply voltages V_{CC} and V_{EE} . The positive peak analog voltage should not exceed V_{CC} . Similarly, the negative peak analog voltage should not go below V_{EE} . In the example below, the difference between V_{CC} and V_{EE} is 12 V.

Therefore, using the configuration in Figure 16, a maximum analog signal of twelve volts peak-to-peak can be controlled.

When voltage transients above V_{CC} and/or below V_{EE} are anticipated on the analog channels, external diodes (Dx) are recommended as shown in Figure 17. These diodes should be small signal, fast turn–on types able to absorb the maximum anticipated current surges during clipping. An alternate method would be to replace the Dx diodes with MOSORBs (MOSORB® is an acronym for high current surge protectors). MOSORBs are fast turn–on devices ideally suited for precise dc protection with no inherent wear out mechanism.

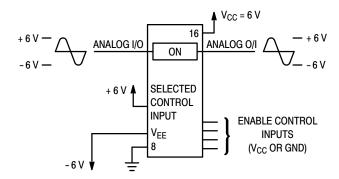


Figure 16.

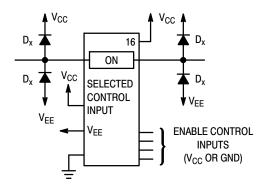


Figure 17. Transient Suppressor Application

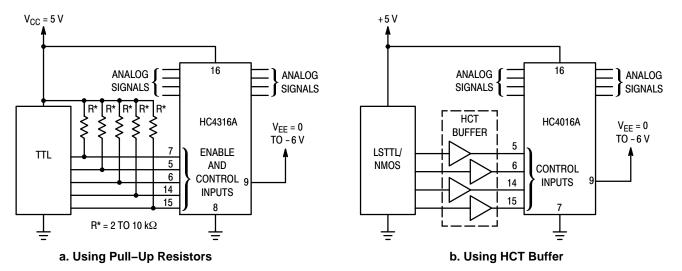


Figure 18. LSTTL/NMOS to HCMOS Interface

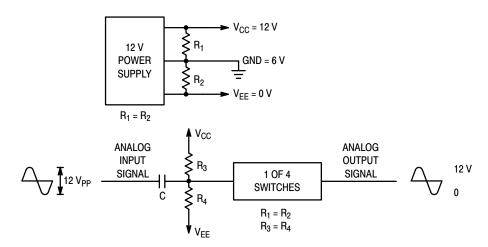


Figure 19. Switching a 0-to-12 V Signal Using a Single Power Supply (GND \neq 0 V)

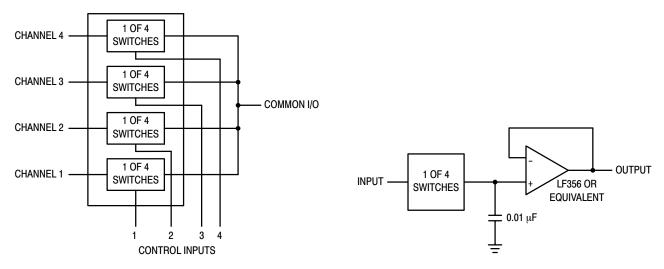


Figure 20. 4-Input Multiplexer

Figure 21. Sample/Hold Amplifier

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MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	#1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION		BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.		7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	OOL DEDING	COOTDONT
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	FOOTPRINT
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		i.40 — →
								- 0	.40
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				10% 1.12
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPU	Τ\		1	16
3.	DRAIN, #2	3.		3.	COMMON DRAIN (OUTPU			, L .	'0
3. 4.	DRAIN, #2	3. 4.	CATHODE	3. 4.	GATE P-CH	1)		- —	
4. 5.	DRAIN, #2	4. 5.	CATHODE	4. 5.	COMMON DRAIN (OUTPU	Τ\		, , , , , , , , , , , , , , , , , , , 	
5. 6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU		16	5X 1 -	
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU		0.5	58	, L
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	•,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU	T)			
11.	GATE, #3	11.		11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3	12.		12.	COMMON DRAIN (OUTPU				
13.	GATE, #2	13.		13.	GATE N-CH	.,			
14.	SOURCE, #2	14.		14.	COMMON DRAIN (OUTPU	T)			V PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU				1 <u>+=</u> 1- 1
16.	SOURCE, #1		ANODE	16.	SOURCE N-CH	.,			
								□ 8	9 + - + -
									~
									' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '
									DIMENSIONS: MILLIMETERS

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DESCRIPTION:	SOIC-16		PAGE 1 OF 1

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